

NTR4502P, NVTR4502P

Power MOSFET

–30 V, –1.95 A, Single, P-Channel, SOT–23

Features

- Leading Planar Technology for Low Gate Charge/Fast Switching
- Low $R_{DS(ON)}$ for Low Conduction Losses
- SOT–23 Surface Mount for Small Footprint (3 x 3 mm)
- NV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free and are RoHS Compliant

Applications

- DC to DC Conversion
- Load/Power Switch for Portables and Computing
- Motherboard, Notebooks, Camcorders, Digital Camera's, etc.
- Battery Charging Circuits

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	–30	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Drain Current (Note 1)	$t < 10\text{ s}$	$T_A = 25^\circ\text{C}$	I_D –1.95 A
		$T_A = 70^\circ\text{C}$	–1.56
Power Dissipation (Note 1)	$t < 10\text{ s}$	P_D	1.25 W
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D –1.13 A
		$T_A = 70^\circ\text{C}$	–0.90
Power Dissipation (Note 1)	Steady State	P_D	0.4 W
Pulsed Drain Current	$t_p = 10\text{ }\mu\text{s}$	I_{DM}	–6.8 A
Operating Junction and Storage Temperature	T_J, T_{STG}	–55 to 150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	–1.25	A
Lead Temperature for Soldering Purposes (1/8 in from case for 10 s)	T_L	260	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	300	$^\circ\text{C/W}$
Junction-to-Ambient – $t = 10\text{ s}$ (Note 1)	$R_{\theta JA}$	100	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).

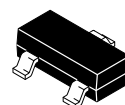
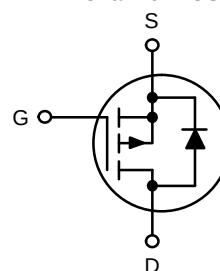


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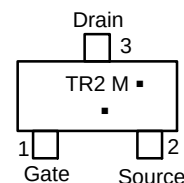
$V_{(BR)DSS}$	$R_{DS(on)}$ TYP	I_D Max (Note 1)
–30 V	155 m Ω @ –10 V	–1.95 A
	240 m Ω @ –4.5 V	

P-Channel MOSFET



SOT–23
CASE 318
STYLE 21

MARKING DIAGRAM/ PIN ASSIGNMENT



TR2 = Device Code
M = Date Code*
■ = Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
NTR4502PT1G	SOT–23 (Pb–Free)	3000 / Tape & Reel
NVTR4502PT1G	SOT–23 (Pb–Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTR4502P, NVTR4502P

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, V_{DS} = -30\text{ V}$	$T_J = 25^\circ\text{C}$		-1	μA
			$T_J = 55^\circ\text{C}$		-10	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-3.0	V
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -1.95\text{ A}$		155	200	$\text{m}\Omega$
		$V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$		240	350	
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{ V}, I_D = -1.25\text{ A}$		3		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1\text{ MHz}, V_{DS} = -15\text{ V}$		200		pF
Output Capacitance	C_{OSS}			80		
Reverse Transfer Capacitance	C_{RSS}			50		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -10\text{ V}, V_{DS} = -15\text{ V}; I_D = -1.95\text{ A}$		6	10	nC
Threshold Gate Charge	$Q_{G(TH)}$			0.3		
Gate-to-Source Charge	Q_{GS}			1		
Gate-to-Drain Charge	Q_{GD}			1.7		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -10\text{ V}, V_{DD} = -15\text{ V}, I_D = -1.95\text{ A}, R_G = 6\text{ }\Omega$		5.2	10	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(OFF)}$			19	35	
Fall Time	t_f			17.5	30	

DRAIN-SOURCE DIODE CHARACTERISTICS (Note 3)

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -1.25\text{ A}$		-0.8	-1.2	V
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, dI_{SD}/dt = 100\text{ A}/\mu\text{s}, I_S = -1.25\text{ A}$		23		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).
- Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

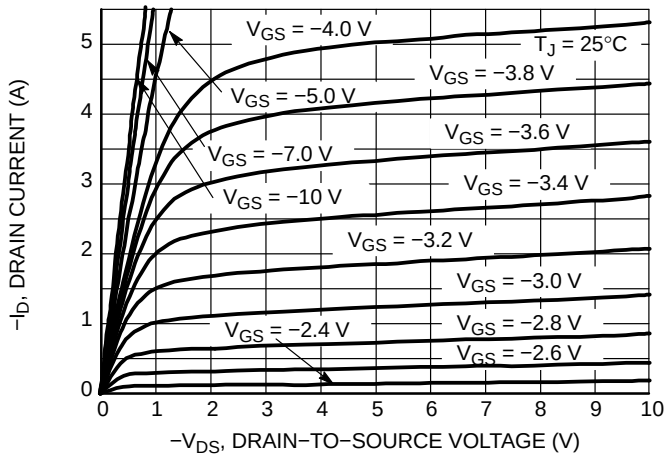


Figure 1. On-Region Characteristics

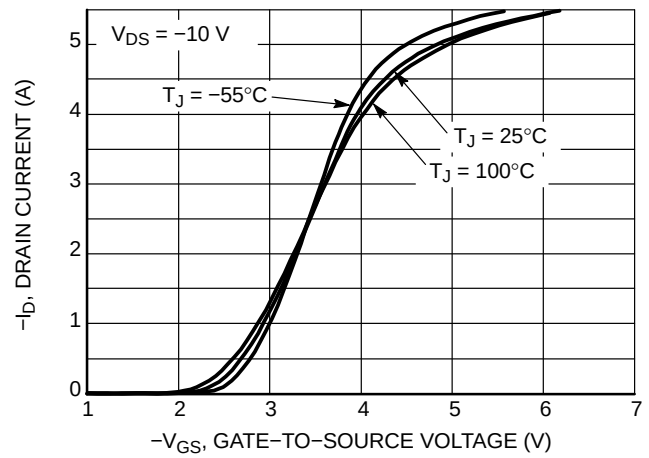


Figure 2. Transfer Characteristics

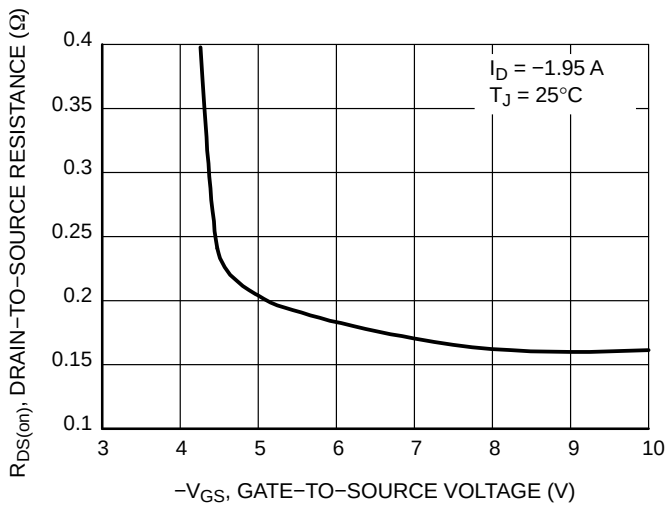


Figure 3. On-Resistance versus Gate-to-Source Voltage

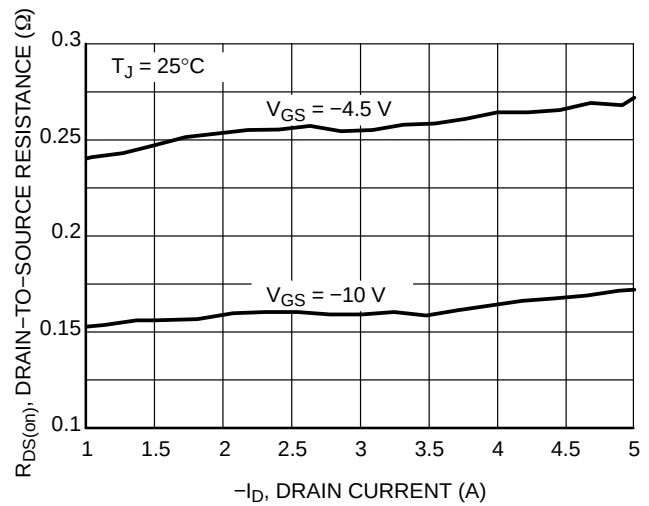


Figure 4. On-Resistance versus Drain Current and Gate Voltage

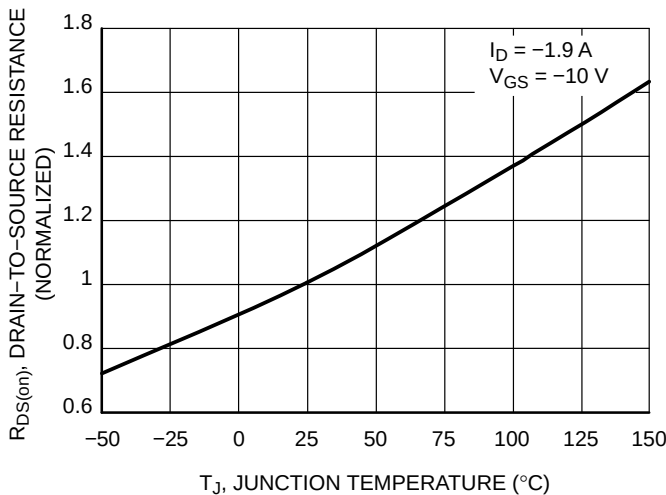


Figure 5. On-Resistance Variation with Temperature

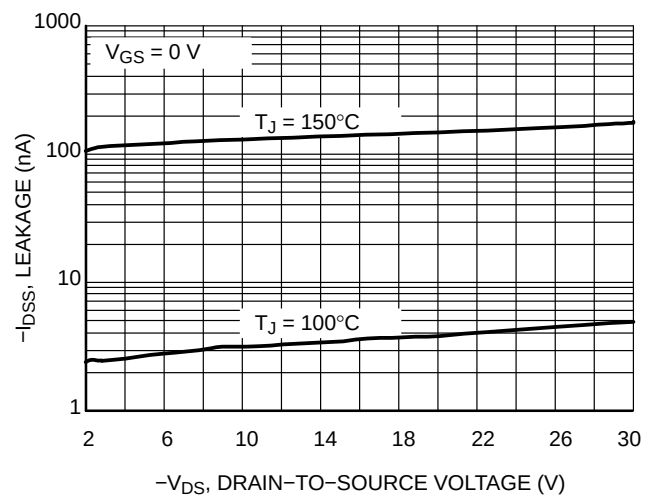


Figure 6. Drain-to-Source Leakage Current versus Voltage

NTR4502P, NVTR4502P

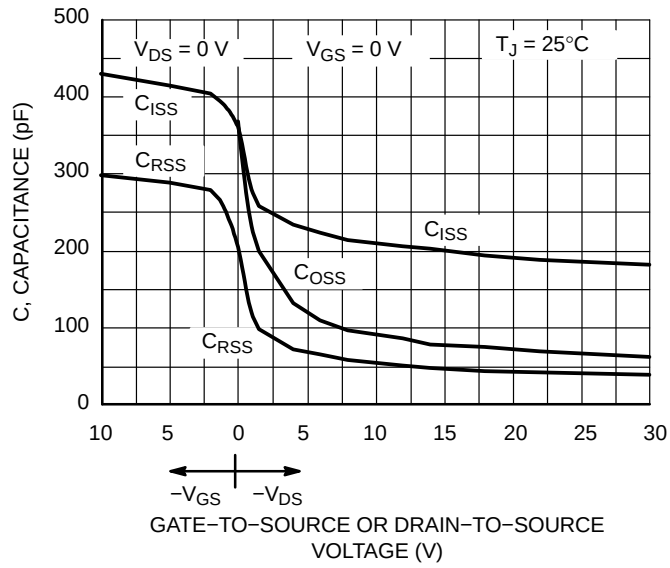


Figure 7. Capacitance Variation

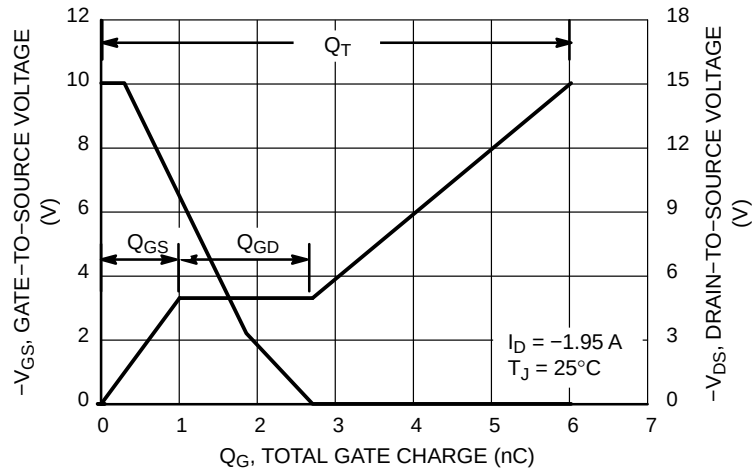


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

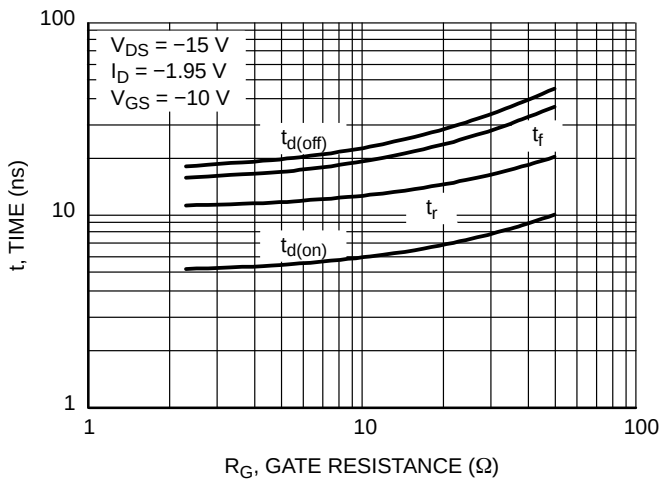


Figure 9. Resistive Switching Time Variation versus Gate Resistance

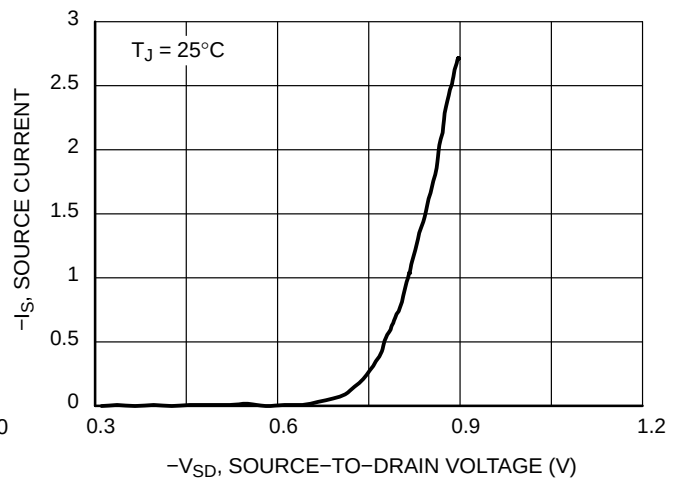
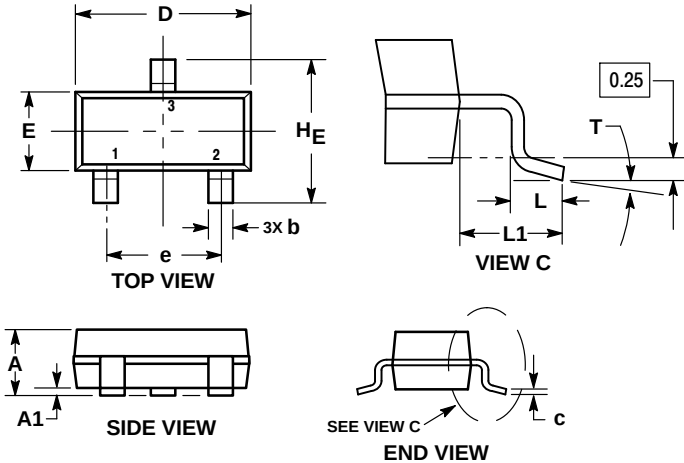


Figure 10. Diode Forward Voltage versus Current

NTR4502P, NVTR4502P

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR

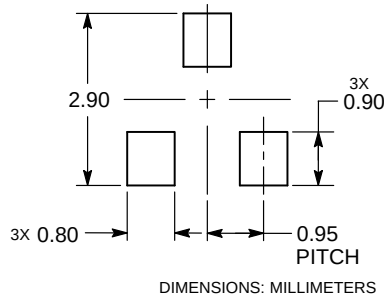


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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